

Docket No.: 50432-293

PATENT

2812

IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

Re Application of

Cyrus E. TABERY, et al.

Serial No.: 10/021,782

Group Art Unit: 2812

Filed: December 18, 2001

Examiner: S.D. Isaac

For: SCANNING LASER THERMAL ANNEALING

THE COMMISSIONER FOR PATENTS AND TRADEMARKS
Washington, DC 20231

Dear Sir:

Transmitted herewith is an Amendment in the above identified application.

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No additional fee is required.

Applicant is entitled to small entity status under 37 CFR 1.27

Also attached:

The fee has been calculated as shown below:

	NO. OF CLAIMS	HIGHEST PREVIOUSLY PAID FOR	EXTRA CLAIMS	RATE	FEE
Total Claims	14	20	0	\$18.00 =	\$0.00
Independent Claims	3	3	0	\$84.00 =	\$0.00
Multiple claims newly presented					\$0.00
Fee for extension of time					\$0.00
					\$0.00
Total of Above Calculations					\$0.00

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Please charge my Deposit Account No. 500417 in the amount of \$0.00. An additional copy of this transmittal sheet is submitted herewith.

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The Commissioner is hereby authorized to charge payment of any fees associated with this communication or credit any overpayment, to Deposit Account No. 500417, including any filing fees under 37 CFR 1.16 for presentation of extra claims and any patent application processing fees under 37 CFR 1.17.

Respectfully submitted,

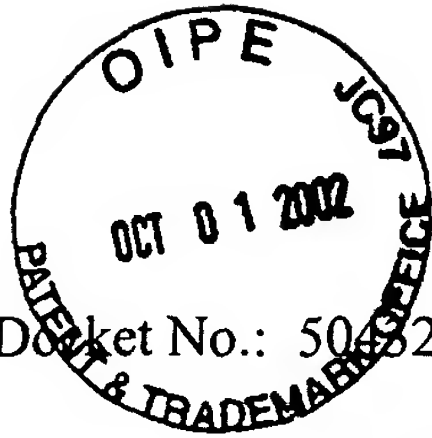
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Docket No.: 50482-293

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IN THE UNITED STATES PATENT AND TRADEMARK OFFICE

In re Application of

Cyrus TABERY, et al.

Application No.: 10/021,782

Filed: December 18, 2001

For: SCANNING LASER THERMAL ANNEALING

Group Art Unit: 2812

Examiner: S.D. Isaac

AMENDMENT

Box Non-Fee Amendment

The Commissioner for Patents and Trademarks
Washington, DC 20231

Sir:

The following Remarks are submitted in response to the Office Action dated July 26, 2002. Please amend the above-identified application as follows:

IN THE CLAIMS:

Please amend claim 11 as follows:

11. (Amended) A method of manufacturing a semiconductor device, comprising the steps of:

forming a gate electrode over a substrate;

introducing ions into the substrate to form source/drain regions in the substrate proximate to the gate electrode;

activating a portion of the source/drain regions by laser thermal annealing using a pulse of laser energy from a laser;

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